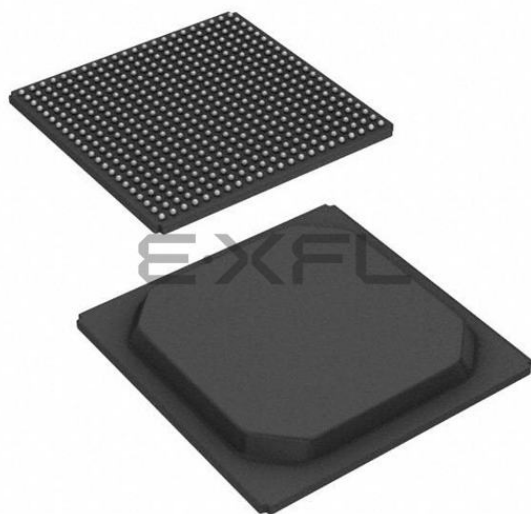




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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	300000
Total RAM Bits	21094400
Number of I/O	244
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA, FCBGA
Supplier Device Package	484-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf300ts-1fcg484i

3 References

The following documents are recommended references. For more information about PolarFire static and dynamic power data, see the [PolarFire Power Estimator Spreadsheet](#).

- [PO0137](#): PolarFire FPGA Product Overview
- [ER0217](#): PolarFire FPGA Pre-Production Device Errata
- [UG0722](#): PolarFire FPGA Packaging and Pin Descriptions Users Guide
- [UG0726](#): PolarFire FPGA Board Design User Guide
- [UG0686](#): PolarFire FPGA User I/O User Guide
- [UG0680](#): PolarFire FPGA Fabric User Guide
- [UG0714](#): PolarFire FPGA Programming User Guide
- [UG0684](#): PolarFire FPGA Clocking Resources User Guide
- [UG0687](#): PolarFire FPGA 1G Ethernet Solutions User Guide
- [UG0727](#): PolarFire FPGA 10G Ethernet Solutions User Guide
- [UG0748](#): PolarFire FPGA Low Power User Guide
- [UG0676](#): PolarFire FPGA DDR Memory Controller User Guide
- [UG0743](#): PolarFire FPGA Debugging User Guide
- [UG0725](#): PolarFire FPGA Device Power-Up and Resets User Guide
- [UG0677](#): PolarFire FPGA Transceiver User Guide
- [UG0685](#): PolarFire FPGA PCI Express User Guide
- [UG0753](#): PolarFire FPGA Security User Guide
- [UG0752](#): PolarFire FPGA Power Estimator User Guide

Parameter	Symbol	Min	Typ	Max	Unit
Transceiver TX and RX lanes supply at 1.05 V mode (when any lane rate is greater than 10.3125 Gbps) ¹	V _{DDA}	1.02	1.05	1.08	V
Programming and HSIO receiver supply	V _{DD18}	1.71	1.80	1.89	V
FPGA core and FPGA PLL high-voltage supply	V _{DD25}	2.425	2.50	2.575	V
Transceiver PLL high-voltage supply	V _{DDA25}	2.425	2.50	2.575	V
Transceiver reference clock supply –3.3 V nominal	V _{DD_XCVR_CLK}	3.135	3.3	3.465	V
Transceiver reference clock supply –2.5 V nominal	V _{DD_XCVR_CLK}	2.375	2.5	2.625	V
Global V _{REF} for transceiver reference clocks ³	XCVR _{VREF}	Ground		V _{DD_XCVR_CLK}	V
HSIO DC I/O supply. Allowed nominal options: 1.2 V, 1.35 V, 1.5 V, and 1.8 V ⁴	V _{DDI_x}	1.14	Various	1.89	V
GPIO DC I/O supply. Allowed nominal options: 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V ^{2,4}	V _{DDI_x}	1.14	Various	3.465	V
Dedicated I/O DC supply for JTAG and SPI (GPIO Bank 3). Allowed nominal options: 1.8 V, 2.5 V, and 3.3 V	V _{DDI3}	1.71	Various	3.465	V
GPIO auxiliary supply for I/O bank x with V _{DDI_x} = 3.3 V nominal ^{2,4}	V _{DDAUX_x}	3.135	3.3	3.465	V
GPIO auxiliary supply for I/O bank x with V _{DDI_x} = 2.5 V nominal or lower ^{2,4}	V _{DDAUX_x}	2.375	2.5	2.625	V
Extended commercial temperature range	T _J	0		100	°C
Industrial temperature range	T _J	–40		100	°C
Extended commercial programming temperature range	T _{PRG}	0		100	°C
Industrial programming temperature range	T _{PRG}	–40		100	°C

1. V_{DD} and V_{DDA} can independently operate at 1.0 V or 1.05 V nominal. These supplies are not dynamically adjustable.
2. For GPIO buffers where I/O bank is designated as bank number, if V_{DDI_x} is 2.5 V nominal or 3.3 V nominal, V_{DDAUX_x} must be connected to the V_{DDI_x} supply for that bank. If V_{DDI_x} for a given GPIO bank is <2.5 V nominal, V_{DDAUX_x} per I/O bank must be powered at 2.5 V nominal.
3. XCVR_{VREF} globally sets the reference voltage of the transceiver's single-ended reference clock input buffers. It is typically near V_{DD_XCVR_CLK}/2 V but is allowed in the specified range.
4. The power supplies for a given I/O bank x are shown as VDDI_x and VDDAUX_x.

Table 8 • Maximum Overshoot During Transitions for GPIO

AC (V _{IN}) Overshoot Duration as % at T _J = 100 °C	Condition (V)
100	3.8
100	3.85
100	3.9
100	3.95
70	4
50	4.05
33	4.1
22	4.15
14	4.2
9.8	4.25
6.5	4.3
4.4	4.35
3	4.4
2	4.45
1.4	4.5
0.9	4.55
0.6	4.6

Note: Overshoot level is for V_{DDI} at 3.3 V.

The following table shows the maximum AC input voltage (V_{IN}) undershoot duration for GPIO.

Table 9 • Maximum Undershoot During Transitions for GPIO

AC (V _{IN}) Undershoot Duration as % at T _J = 100 °C	Condition (V)
100	-0.5
100	-0.55
100	-0.6
100	-0.65
100	-0.7
100	-0.75
100	-0.8
100	-0.85
100	-0.9
100	-0.95
100	-1
100	-1.05
100	-1.1
100	-1.15
100	-1.2
69	-1.25
45	-1.3

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
HSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSTL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL12II ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL18I ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /55	(V _{DDI} – V _{OH}) /55
HSUL18II ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH}) /40
POD12I ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /48	(V _{DDI} – V _{OH}) /48
POD12II ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /34	(V _{DDI} – V _{OH}) /34

1. Drive strengths per PCI specification V/I curves.
2. Refer to [UG0686: PolarFire FPGA User I/O User Guide](#) for details on supported drive strengths.
3. For external stub-series resistance. This resistance is on-die for GPIO.
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).
5. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
6. The total DC sink/source current of all IOs within a lane is limited as follows:
 - a. HSIO lane: 120 mA per 12 IO buffers.
 - b. GPIO lane: 160 mA per 12 IO buffers.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

6.3.2 Differential DC Input and Output Levels

The follow tables list the differential DC I/O levels.

Table 14 • Differential DC Input Levels

I/O Standard	Bank Type	VICM_RANGE Libero Setting	V _{ICM} ^{1,3} Min (V)	V _{ICM} ^{1,3} Typ (V)	V _{ICM} ^{1,3} Max (V)	V _{ID} ² Min (V)	V _{ID} Typ (V)	V _{ID} Max (V)
LVDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS18 ⁴	GPIO	Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6

Table 17 • Complementary Differential DC Output Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} ^{1,3} Min (V)	I _{OL} ² Min (mA)	I _{OH} ² Min (mA)
SSTL25I	2.375	2.5	2.625		V _{TT} – 0.608	V _{TT} + 0.608	8.1	8.1
SSTL25II	2.375	2.5	2.625		V _{TT} – 0.810	V _{TT} + 0.810	16.2	16.2
SSTL18I	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603	6.7	6.7
SSTL18II	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603	13.4	13.4
SSTL15I ⁴	1.425	1.5	1.575		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL15II ⁴	1.425	1.5	1.575		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /34	(V _{DDI} – V _{OH})/34
SSTL135I ⁴	1.283	1.35	1.418		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL135II ⁴	1.283	1.35	1.418		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /34	(V _{DDI} – V _{OH})/34
HSTL15I	1.425	1.5	1.575		0.4	V _{DDI} – 0.4	8	8
HSTL15II	1.425	1.5	1.575		0.4	V _{DDI} – 0.4	16	16
HSTL135I ⁴	1.283	1.35	1.418		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /50	(V _{DDI} – V _{OH})/50
HSTL135II ⁴	1.283	1.35	1.418		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /25	(V _{DDI} – V _{OH})/25
HSTL12I ⁴	1.14	1.2	1.26		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /50	(V _{DDI} – V _{OH})/50
HSUL18I ⁴	1.71	1.8	1.89		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /55	(V _{DDI} – V _{OH})/55
HSUL18II ⁴	1.71	1.8	1.89		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /25	(V _{DDI} – V _{OH})/25
HSUL12I ⁴	1.14	1.2	1.26		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /40	(V _{DDI} – V _{OH})/40
POD12I ^{3,4}	1.14	1.2	1.26		0.5 × V _{DDI}		V _{OL} /48	(V _{DDI} – V _{OH})/48
POD12II ^{3,4}	1.14	1.2	1.26		0.5 × V _{DDI}		V _{OL} /34	(V _{DDI} – V _{OH})/34

1. V_{OH} is the single-ended high-output voltage.
2. The total DC sink/source current of all IOs within a lane is limited as follows:
 - a. HSIO lane: 120 mA per 12 IO buffers.
 - b. GPIO lane: 160 mA per 12 IO buffers
3. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).

6.3.4 HSIO On-Die Termination

The following tables lists the on-die termination calibration accuracy specifications for HSIO bank.

Table 18 • Single-Ended Thevenin Termination (Internal Parallel Thevenin Termination)

Min (%)	Typ	Max (%)	Unit	Condition
–40	50	20	Ω	V _{DDI} = 1.8 V/1.5 V/1.35 V/1.2 V
–40	75	20	Ω	V _{DDI} = 1.8 V
–40	150	20	Ω	V _{DDI} = 1.8 V
–20	20	20	Ω	V _{DDI} = 1.5 V/1.35 V
–20	30	20	Ω	V _{DDI} = 1.5 V/1.35 V
–20	40	20	Ω	V _{DDI} = 1.5 V/1.35 V
–20	60	20	Ω	V _{DDI} = 1.5 V/1.35 V
–20	120	20	Ω	V _{DDI} = 1.5 V/1.35 V

Standard	STD	–1	Unit
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL12	1066	1333	Mbps
HSTL12	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVC MOS18 (12 mA)	500	500	Mbps
LVC MOS15 (10 mA)	500	500	Mbps
LVC MOS12 (8 mA)	300	300	Mbps

1. Performance is achieved with $V_{ID} \geq 200$ mV.

Table 25 • GPIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS25/LVDS33/LCMDS25/LCMDS33	1250	1600	Mbps
RSDS25/RSDS33	800	800	Mbps
MINILVDS25/MINILVDS33	800	800	Mbps
SUBLVDS25/SUBLVDS33	800	800	Mbps
PPDS25/PPDS33	800	800	Mbps
SLVS25/SLVS33	800	800	Mbps
SLVSE15	800	800	Mbps
HCSL25/HCSL33	800	800	Mbps
BUSLVDSE25	800	800	Mbps
MLVDSE25	800	800	Mbps
LVPECL33	800	800	Mbps
SSTL25I	800	800	Mbps
SSTL25II	800	800	Mbps
SSTL18I	800	800	Mbps
SSTL18II	800	800	Mbps
SSTL15I	800	1066	Mbps
SSTL15II	800	1066	Mbps
HSTL15I	800	900	Mbps
HSTL15II	800	900	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
PCI	500	500	Mbps
LVTTTL33 (20 mA)	500	500	Mbps
LVC MOS33 (20 mA)	500	500	Mbps
LVC MOS25 (16 mA)	500	500	Mbps

7.1.6 User I/O Switching Characteristics

The following section describes characteristics for user I/O switching.

For more information about user I/O timing, see the *PolarFire I/O Timing Spreadsheet* (to be released).

7.1.6.1 I/O Digital

The following tables provide information about I/O digital.

Table 30 • I/O Digital Receive Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
F _{MAX}	RX_SDR_G_A	Rx SDR							MHz	From a global clock source, aligned
F _{MAX}	RX_SDR_L_A	Rx SDR							MHz	From a lane clock source, aligned
F _{MAX}	RX_SDR_G_C	Rx SDR							MHz	From a global clock source, centered
F _{MAX}	RX_SDR_L_C	Rx SDR							MHz	From a lane clock source, centered

Table 31 • I/O Digital Receive Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
F _{MAX}	RX_DDR_G_A	Rx DDR		335			335	MHz	MHz	From a global clock source, aligned
F _{MAX}	RX_DDR_L_A	Rx DDR		250			250		MHz	From a lane clock source, aligned
F _{MAX}	RX_DDR_G_C	Rx DDR		335			335		MHz	From a global clock source, centered
F _{MAX}	RX_DDR_L_C	Rx DDR		250			250		MHz	From a lane clock source, centered
F _{MAX} 2:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Clock-to-Data Condition
F _{MAX} 4:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 8:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 2:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 4:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 8:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 2:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 4:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 8:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 2:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 4:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Forwarded Clock-to-Data Skew
Output F _{MAX} 2:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F _{MAX} 4:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F _{MAX} 8:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
In delay, out delay, DLL delay step sizes			12.7	30	35	12.7	25	29.5	ps	

Table 34 • I/O CDR Switching Characteristics

Parameter	Min	Max	Unit
Data rate	266	1250	Mbps
Receiver Sinusoidal jitter tolerance ¹	0.2		UI

1. Jitter values based on bit error ratio (BER) of 10–12, 80 MHz sinusoidal jitter injected to Rx data.

Note: See the LVDS output buffer specifications for transmit characteristics.

7.2 Clocking Specifications

This section describes the PLL and DLL clocking and oscillator specifications.

7.2.1 Clocking

The following table provides clocking specifications.

Table 35 • Global and Regional Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Global clock F _{MAX}	F _{MAXG}	500	500	500	500	MHz	
Regional clock F _{MAX}	F _{MAXR}	375	375	375	375	MHz	Transceiver interfaces only
	F _{MAXR}	250	250	250	250	MHz	All other interfaces
Global clock duty cycle distortion	T _{DCDG}	190	190	190	190	ps	At 500 MHz

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Regional clock duty cycle distortion	T _{DCDR}	120	120	120	120	ps	At 250 MHz

The following table provides clocking specifications from –40 °C to 100 °C.

Table 36 • High-Speed I/O Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
High-speed I/O clock F _{MAX}	F _{MAXB}	1000	1250	1000	1250	MHz	HSIO and GPIO
High-speed I/O clock skew ¹	F _{SKEWB}	30	20	30	20	ps	HSIO without bridging
	F _{SKEWB}	600	500	600	500	ps	HSIO with bridging
	F _{SKEWB}	45	35	45	35	ps	GPIO without bridging
	F _{SKEWB}	75	60	75	60	ps	GPIO with bridging
High-speed I/O clock duty cycle distortion ²	T _{DCB}	90	90	90	90	ps	HSIO without bridging
	T _{DCB}	115	115	115	115	ps	HSIO with bridging
	T _{DCB}	90	90	90	90	ps	GPIO without bridging
	T _{DCB}	115	115	115	115	ps	GPIO with bridging

1. F_{SKEWB} is the worst-case clock-tree skew observable between sequential I/O elements. Clock-tree skew is significantly smaller at I/O registers close to each other and fed by the same or adjacent clock-tree branches. Use the Microsemi Timing Analyzer tool to evaluate clock skew specific to the design.
2. Parameters listed in this table correspond to the worst-case duty cycle distortion observable at the I/O flip flops. IBIS should be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times for any I/O standard.

7.2.2

PLL

The following table provides information about PLL.

Table 37 • PLL Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Input clock frequency (integer mode)	F _{INI}	1		1250	MHz
Input clock frequency (fractional mode)	F _{INF}	10		1250	MHz
Minimum reference or feedback pulse width ¹	F _{INPULSE}	200			ps
Frequency at the Frequency Phase Detector (PFD) (integer mode)	F _{PHDET1}	1		312	MHz
Frequency at the PFD (fractional mode)	F _{PHDET2}	10	50	125	MHz
Allowable input duty cycle	F _{INDUTY}	25		75	%

Parameter ¹	Symbol	Min	Typ	Max	Unit
Secondary output clock frequency ²	F _{OUTSF}	33.3		800	MHz
Input clock cycle-to-cycle jitter	F _{INJ}			200	ps
Output clock period cycle-to-cycle jitter (w/clean input)	T _{OUTJITTERP}			300	ps
Output clock-to-clock skew between two outputs with the same phase settings	T _{SKEW}			±200	ps
DLL lock time	T _{LOCK}	16		16K	Reference clock cycles
Minimum reset pulse width	T _{MRPW}	3			ns
Minimum input pulse width ³	T _{MIPW}	20			ns
Minimum input clock pulse width high	T _{MPWH}	400			ps
Minimum input clock pulse width low	T _{MPWL}	400			ps
Delay step size	T _{DEL}	12.7	30	35	ps
Maximum delay block delay ⁴	T _{DELMAX}	1.8		4.8	ns
Output clock duty cycle (with 50% duty cycle input) ⁵	T _{DUTY}	40		60	%
Output clock duty cycle (in phase reference mode) ⁵	T _{DUTY50}	45		55	%

1. For all DLL modes.
2. Secondary output clock divided by four option.
3. On load, direction, move, hold, and update input signals.
4. 128 delay taps in one delay block.
5. Without duty cycle correction enabled.

7.2.4

RC Oscillators

The following tables provide internal RC clock resources for user designs and additional information about designing systems with RF front end information about emitters generated on-chip to support programming operations.

Table 39 • 2 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC _{2FREQ}		2		MHz
Accuracy	RC _{2FACC}	−4		4	%
Duty cycle	RC _{2DC}	46		54	%
Peak-to-peak output period jitter	RC _{2PJIT}		5	10	ns
Peak-to-peak output cycle-to-cycle jitter	RC _{2CIIT}		5	10	ns
Operating current (V _{DD25})	RC _{2IVPPA}			60	μA
Operating current (V _{DD})	RC _{2IVDD}			2.6	μA

Table 40 • 160 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC _{SCFREQ}		160		MHz
Accuracy	RC _{SCFACC}	−4		4	%
Duty cycle	RC _{SCDC}	47		52	%
Peak-to-peak output period jitter	RC _{SCPJIT}			600	ps
Peak-to-peak output cycle-to-cycle jitter	RC _{SCCIIT}			172	ps
Operating current (V _{DD25})	RC _{SCVPPA}			599	μA

7.3 Fabric Specifications

The following section describes specifications for the fabric.

7.3.1 Math Blocks

The following tables describe math block performance.

Table 41 • Math Block Performance Extended Commercial Range (0 °C to 100 °C)

Parameter	Symbol	Modes	V _{DD} = 1.0 V – STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V – STD	V _{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F _{MAX}	18 × 18 multiplication	370	470	440	500	MHz
		18 × 18 multiplication summed with 48-bit input	370	470	440	500	MHz
		18 × 19 multiplier pre-adder ROM mode	365	465	435	500	MHz
		Two 9 × 9 multiplication	370	470	440	500	MHz
		9 × 9 dot product (DOTP)	370	470	440	500	MHz
		Complex 18 × 19 multiplication	360	455	430	500	MHz

Table 42 • Math Block Performance Industrial Range (–40 °C to 100 °C)

Parameter	Symbol	Modes	V _{DD} = 1.0 V – STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V – STD	V _{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F _{MAX}	18 × 18 multiplication	365	465	435	500	MHz
		18 × 18 multiplication summed with 48-bit input	365	465	435	500	MHz
		18 × 19 multiplier pre-adder ROM mode	355	460	430	500	MHz
		Two 9 × 9 multiplication	365	465	435	500	MHz
		9 × 9 DOTP	365	465	435	500	MHz
		Complex 18 × 19 multiplication	350	450	425	500	MHz

Table 52 • PolarFire Transceiver Transmitter Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Differential termination	V_{TERM}		85		Ω	
	V_{TERM}		100		Ω	
	V_{TERM}		150		Ω	
Common mode voltage ¹	V_{OCM}	$0.44 \times V_{\text{DDA}}$	$0.525 \times V_{\text{DDA}}$	$0.59 \times V_{\text{DDA}}$	V	DC coupled 50% setting
	V_{OCM}	$0.52 \times V_{\text{DDA}}$	$0.6 \times V_{\text{DDA}}$	$0.66 \times V_{\text{DDA}}$	V	DC coupled 60% setting
	V_{OCM}	$0.61 \times V_{\text{DDA}}$	$0.7 \times V_{\text{DDA}}$	$0.75 \times V_{\text{DDA}}$	V	DC coupled 70% setting
	V_{OCM}	$0.63 \times V_{\text{DDA}}$	$0.8 \times V_{\text{DDA}}$	$0.83 \times V_{\text{DDA}}$	V	DC coupled 80% setting
Rise time ²	T_{TXRF}	41		70	ps	20% to 80%
Fall time ²		41		70	ps	80% to 20%
Differential peak-to-peak amplitude	V_{ODPP}		1040		mV	1000 mV setting
	V_{ODPP}		840		mV	800 mV setting
	V_{ODPP}		630		mV	600 mV setting
	V_{ODPP}		620		mV	500 mV setting
	V_{ODPP}		530		mV	400 mV setting
	V_{ODPP}		360		mV	300 mV setting
	V_{ODPP}		240		mV	200 mV setting
	V_{ODPP}		160		mV	100 mV setting
Transmit lane P to N skew ³	T_{OSKEW}		8	15	ps	
Lane to lane transmit skew ⁴	T_{LLSKEW}			75	ps	Single PLL
					ps	Multiple PLL
Electrical idle transition entry time ⁷	$T_{\text{TxElTrEntry}}$				ns	
Electrical idle transition exit time ⁷	$T_{\text{TxElTrExit}}$				ns	
Electrical idle amplitude	V_{TxElpp}				mV	
TXPLL lock time	T_{TXLock}			1600	PFD cycles	
Digital PLL lock time ⁸	T_{DPLLlock}				REFCLK UIs	
Total jitter ^{5,6}	T_{J}				UI	Data rate ≥ 8.5 Gbps to 12.7 Gbps ⁹
Deterministic jitter ^{5,6}	T_{DJ}				UI	(Tx V_{CO} rate 4.25 GHz to 6.35 GHz)
Total jitter ^{5,6}	T_{J}			0.28	UI	Data rate ≥ 3.2 Gbps to 8.5 Gbps
Deterministic jitter ^{5,6}	T_{DJ}			0.07	UI	(Tx V_{CO} rate 2.5 GHz to 5.0 GHz)
Total jitter ^{5,6}	T_{J}			0.28	UI	Data rate ≥ 1.6 Gbps to 3.2 Gbps
Deterministic jitter ^{5,6}	T_{DJ}			0.07	UI	(Tx V_{CO} rate 2.5 GHz to 5.0 GHz)
Total jitter ^{5,6}	T_{J}			0.13	UI	Data rate ≥ 800 Mbps to 1.6 Gbps
Deterministic jitter ^{5,6}	T_{DJ}			0.02	UI	(Tx V_{CO} rate 2.5 GHz to 5.0 GHz)
Total jitter ^{5,6}	T_{J}			0.06	UI	Data rate = 250 Mbps to 800 Mbps
Deterministic jitter ^{5,6}	T_{DJ}			0.01	UI	(Tx V_{CO} rate 2.5 GHz to 5.0 GHz)

1. Increased DC common mode settings above 50% reduce allowed V_{OD} output swing capabilities.
2. Adjustable through transmit emphasis.
3. With estimated package differences.
4. Single PLL applies to all four lanes in the same quad location with the same TxPLL.

Table 55 • PCI Express Gen2

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	5.0 Gbps		0.35	UI
Receiver jitter tolerance	5.0 Gbps	0.4		UI

Note: With add-in card as specified in PCI Express CEM Rev 2.0.

7.5.2 Interlaken

The following table describes Interlaken.

Table 56 • Interlaken

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	6.375 Gbps		0.3	UI
	10.3125 Gbps		0.3	UI
	12.7 Gbps ¹			UI
Receiver jitter tolerance	6.375 Gbps	0.6		UI
	10.3125 Gbps	0.65		UI
	12.7 Gbps ¹			UI

- For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions](#) (see page 6).

7.5.3 10GbE (10GBASE-R, and 10GBASE-KR)

The following table describes 10GbE (10GBASE-R).

Table 57 • 10GbE (10GBASE-R)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	10.3125 Gbps		0.28	UI
Receiver jitter tolerance	10.3125 Gbps	0.7		UI

The following table describes 10GbE (10GBASE-KR).

Table 58 • 10GbE (10GBASE-KR)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	10.3125 Gbps			UI
Receiver jitter tolerance	10.3125 Gbps			UI

The following table describes 10GbE (XAUI).

Table 59 • 10GbE (XAUI)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter (near end)	3.125 Gbps		0.35	UI
Total transmit jitter (far end)			0.55	UI
Receiver jitter tolerance	3.125 Gbps	0.65		UI

The following table describes 10GbE (RXAUI).

Parameter	Typ	Max	Unit	Conditions
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ¹			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

7.6.7 Verify Time

The following tables describe verify time.

Table 81 • Standalone Fabric Verify Times

Parameter	Devices	Max	Unit
Standalone verification over JTAG	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	53 ¹	s
	MPF300T, TL, TS, TLS	90 ¹	s
	MPF500T, TL, TS, TLS		s
Standalone verification over SPI	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	37 ²	s
	MPF300T, TL, TS, TLS	55 ²	s
	MPF500T, TL, TS, TLS		s

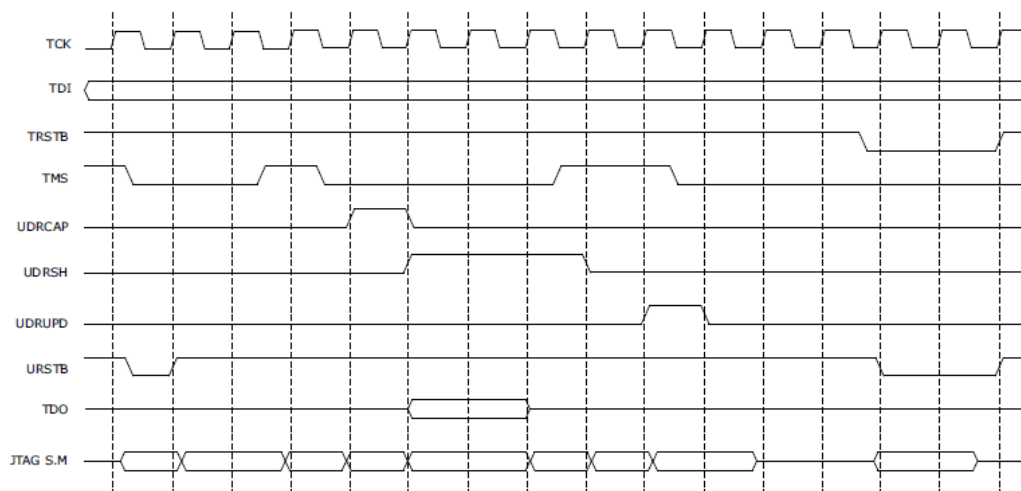
1. Programmer: FlashPro5, TCK 10 MHz; PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.
2. SmartFusion2 with MSS running at 100 MHz, MSS_SPI_0 port running at 6.67 MHz. DirectC version 4.1.

Notes:

- Standalone verify is limited to 2,000 total device hours over the industrial –40 °C to 100 °C temperature.
- Use the digest system service, for verify device time more than 2,000 hours.
- Standalone verify checks the programming margin on both the P and N gates of the push-pull cell.
- Digest checks only the P side of the push-pull gate. However, the push-pull gates work in tandem. Digest check is recommended if users believe they will exceed the 2,000-hour verify time specification.

Table 82 • Verify Time by Programming Hardware

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF100T, TL, TS, TLS						
MPF200T, TL, TS, TLS	9	67	53			s
MPF300T, TL, TS, TLS	14	95	90			s

Figure 3 • UJTAG Timing Diagram

7.8.2 UJTAG_SEC Switching Characteristics

The following table describes characteristics of UJTAG_SEC switching.

Table 89 • UJTAG Security Performance Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	F _{TCK}				MHz	

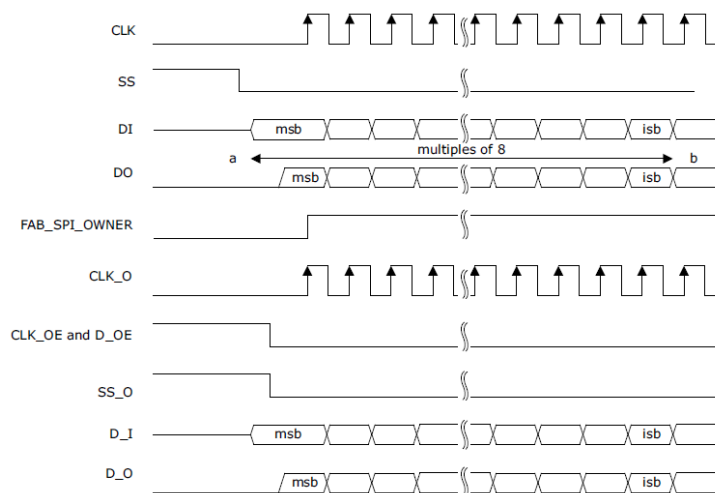
7.8.3 USPI Switching Characteristics

The following section describes characteristics of USPI switching.

Table 90 • SPI Macro Interface Timing Characteristics

Parameter	Symbol	V _{DDI} = 3.3 V Max	V _{DDI} = 2.5 V Max	V _{DDI} = 1.8 V Max	V _{DDI} = 1.5 V Max	V _{DDI} = 1.2 V Max	Unit
Propagation delay from the fabric to pins ¹	TPD_MOSI	0.8	1	1.2	1.4	1.6	ns
	TPD_MISO	3.5	3.75	4	4.25	4.5	ns
	TPD_SS	3.5	3.75	4	4.25	4.5	ns
	TPD_SCK	3.5	3.75	4	4.25	4.5	ns
	TPD_MOSI_OE	3.5	3.75	4	4.25	4.5	ns
	TPD_SS_OE	3.5	3.75	4	4.25	4.5	ns
	TPD_SCK_OE	3.5	3.75	4	4.25	4.5	ns

1. Assumes CL of the relevant I/O standard as described in the input and output delay measurement tables.

Figure 4 • USPI Switching Characteristics

7.8.4

Tamper Detectors

The following section describes tamper detectors.

Table 91 • ADC Conversion Rate

Parameter	Description	Min	Typ ¹	Max
T _{CONV1}	Time from enable changing from zero to non-zero value to first conversion completes. Minimum value applies when POWEROFF = 0.	420 μs		470 μs
T _{CONVN}	Time between subsequent channel conversions.		480 μs	
T _{SETUP}	Data channel and output to valid asserted. Data is held until next conversion completes, that is >480 μs.	0 ns		
T _{VALID} ²	Width of the valid pulse.	1.625 μs		2 μs
T _{RATE}	Time from start of first set of conversions to the start of the next set. Can be considered as the conversion rate. Is set by the conversion rate parameter.	480 μs	Rate × 32 μs	8128 μs

1. Min, typ, and max refer to variation due to functional configuration and the raw TVS value. The actual internal correction time will vary based on the raw TVS value.
2. The pulse width varies depending on the time taken to complete the internal calibration multiplication, this can be up to 375 ns.

Note: Once the TVS block is active, the enable signal is sampled 25 ns before the falling edge of valid. The next enabled channel in the sequence 0-1-2-3 is started; that is, if channel 0 has just completed and only channels 0 and 3 are enabled, the next channel will be 3. When all the enabled channels in the sequence 0-1-2-3 are completed, the TVS waits for the conversion rate timer to expire. The enable signal may be changed at any time if it changes to 4'b0000 while valid is asserted (and 25 ns before valid is de-asserted), then no further conversions will be started.

Table 92 • Temperature and Voltage Sensor Electrical Characteristics

Parameter	Min	Typ	Max	Unit	Condition
Temperature sensing range	-40		125	°C	
Temperature sensing accuracy	-10		10	°C	

Table 101 • Cold and Warm Boot

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from T _{FAB_READY} to ready to program through JTAG/SPI-Slave		0	0	0	ms	
The time from T _{FAB_READY} to auto-update start			T _{PUF_OVHD} ¹	T _{PUF_OVHD} ¹	ms	
The time from T _{FAB_READY} to programming recovery start			T _{PUF_OVHD} ¹	T _{PUF_OVHD} ¹	ms	
The time from T _{FAB_READY} to the tamper flags being available	T _{TAMPER_READY}	0	0	0	ms	
The time from T _{FAB_READY} to the Athena Crypto co-processor being available (for S devices only)	T _{CRYPTO_READY}	0	0	0	ms	

1. Programming depends on the PUF to power up. Refer to T_{PUF_OVHD} at section [Secure NVM Performance](#) (see page 58).

7.9.8 I/O Calibration

The following tables specify the initial I/O calibration time for the fastest and slowest supported VDDI ramp times of 0.2 ms to 50 ms, respectively. This only applies to I/O banks specified by the user to be auto-calibrated.

Table 102 • I/O Initial Calibration Time (TCALIB)

Ramp Time	Min (ms)	Max (ms)	Condition
0.2 ms	0.98	2.63	Applies to HSIO and GPIO banks
50 ms	41.62	62.19	Applies to HSIO and GPIO banks

Notes:

- The user may specify any VDDI ramp time in the range specified above. The nominal initial calibration time is given by the specified VDDI ramp time plus 2 ms.
- In order for IO calibration to start, VDDI and VDDAUX of the I/O bank must be higher than the trip point levels specified in [I/O-Related Supplies](#) (see page 66).

Table 103 • I/O Fast Recalibration Time (TRECALIB)

I/O Type	Min (ms)	Typ (ms)	Max (ms)	Condition
GPIO bank	0.16	0.20	0.24	GPIO configured for 3.3 V operation
HSIO bank	0.20	0.25	0.30	HSIO configured for 1.8 V operation

Note: In order to obtain fast re-calibration, the user must assert the relevant clock request signal from the FPGA fabric to the I/O bank controller.

The following table describes the time to enter Flash*Freeze Mode and to exit Flash*Freeze mode.

7.11 User Crypto

The following section describes user crypto.

7.11.1 TeraFire 5200B Switching Characteristics

The following table describes TeraFire 5200B switching characteristics.

Table 112 • TeraFire F5200B Switching Characteristics

Parameter	Symbol	VDD = 1.0 V STD	VDD = 1.0 V – 1	VDD = 1.05 V STD	VDD = 1.05 V – 1	Unit	Condition
Operating frequency	F _{MAX}	189		189		MHz	–40 °C to 100 °C

7.11.2 TeraFire 5200B Throughput Characteristics

The following tables for each algorithm describe the TeraFire 5200B throughput characteristics.

Note: Throughput cycle count collected with Athena TeraFire Core and RISCv running at 100 MHz.

Table 113 • AES

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-ECB-128 encrypt ¹	128	515	1095
	64K	50157	933
AES-ECB-128 decrypt ¹	128	557	1760
	64K	48385	1524
AES-ECB-256 encrypt ¹	128	531	1203
	64K	58349	1203
AES-ECB-256 decrypt ¹	128	589	1676
	64K	56673	1671
AES-CBC-256 encrypt ¹	128	576	1169
	64K	52547	1169
AES-CBC-256 decrypt ¹	128	585	1744
	64K	48565	1652
AES-GCM-128 encrypt ¹ , 128-bit tag, (full message encrypted/authenticated)	128	1925	2740
	64K	60070	2158
AES-GCM-256 encrypt ¹ , 128-bit tag, (full message encrypted/authenticated)	128	1973	2268
	64K	60102	2151

1. With DPA counter measures.

Table 114 • GMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-GCM-256 ¹ , 128-bit tag, (message is only authenticated)	128	1863	2211
	64K	49707	2128

**Microsemi Headquarters**

One Enterprise, Aliso Viejo,
CA 92656 USA
Within the USA: +1 (800) 713-4113
Outside the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996
Email: sales.support@microsemi.com
www.microsemi.com

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